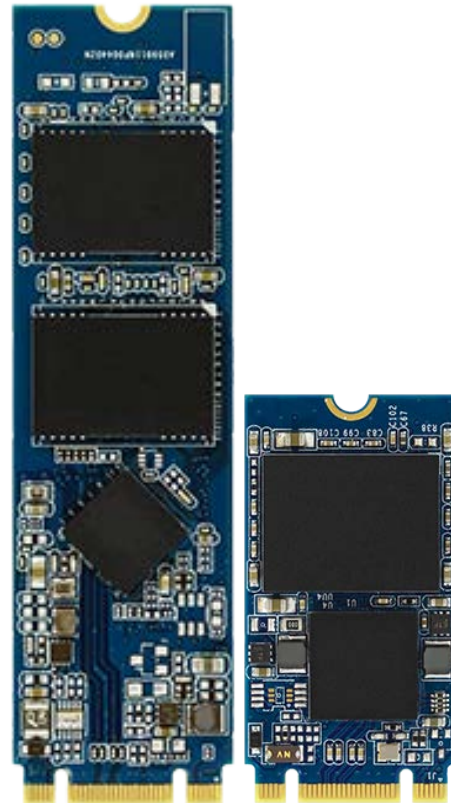


3D NAND Flash

M.2 SATA III Module

PHANES-K Series

M.2 2242 / 2280 Type



Document No. : 100-xBMDS-PKCT3

Version No. : 02V0

Date: June, 2019

ISO 9001 : 2015 CERTIFIED



Product Features

■ Flash IC

- TOSHIBA **BICS FLASH**^{TM,3}
- 3D NAND Flash

■ Compatibility

- Compliant with SATA Revision 3.2
- SATA 1.5Gbps/3.0Gbps/6.0Gbps data transfer rate.
- ATA-8 ACS4 command set

■ Additional Capabilities

- S.M.A.R.T.*¹ (Self-Monitoring, Analysis and Reporting Technology) feature set support.
- Native Command Queuing (NCQ) support.
- TRIM maintenance command support.
- Both Static & Dynamic wear-leveling algorithm
- Hardware Low Density Parity Check Code, LDPC support.

■ Mechanical

- Interface compatible with PCI ExpressTM M.2 (2242/2280)
- M.2 keying notches in B and M positions.
- Dimension:
2242: 42 mm x 22 mm.
2280: 80 mm x 22 mm.
- Weight:
2242: 5.00 g / 0.17 oz.
2280: 8.00 g / 0.28 oz.

■ Power Operating Voltage 3.3V(+/-) 5%

- **2242 Type**

Read Mode: 1,230mW (max.)
Write Mode: 1,336mW (max.)
Idle Mode: 290mW (max.)

- **2280 Type**

Read Mode: 1,475mW (max.)
Write Mode: 1,350mW (max.)
Idle Mode: 277mW (max.)

■ Performance (Maximum value)^{2,}

2242 Type

- Sequential Read: 550.0 MB/sec. (max.)
- Sequential Write: 450.0 MB/sec. (max.)

2280 Type

- Sequential Read: 550.0 MB/sec. (max.)
- Sequential Write: 500.0 MB/sec. (max.)

■ Capacity

- **2242:** 32GB, 64GB and 128GB.
- **2280:** 128GB, 256GB, 512GB and 1TB.

■ Reliability

- **TBW:** Up to 835 TBW at 1TB Capacity.
(Client workload by JESD-219A)
- **ECC:** Designed with hardware LDPC ECC engine with hard-decision and soft-decision decoding.
- **Temperature:** (Operating)
Standard Grade: 0°C ~ +70°C
Wide Temp. Grade: -40°C ~ +85°C
- **Vibration:** 80 Hz to 2000 Hz, 20G, 3 axes
- **Shock:** 0.5ms, 1500 G, 3 axes

■ Certifications and Declarations

- **Certifications:** CE & FCC
- **Declarations:** RoHS & REACH

Remarks:


1. Support official S.M.A.R.T. Utility.
2. Sequential performance is based on CrystalDiskMark 5.1.2 with file size 1000MB
3. **BICS** means Bit Cost Scalable Technology.

BICS FLASH is a trademark of Toshiba Corporation.


Order Information

I. Part Number List

◆ APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series – 2242 Form-factor

Product Picture	Grade	Standard grade (0°C ~ 70°C)	Wide Temp. Grade (-40°C ~ +85°C)
	32GB	SBMDS032G-PKCT34BM	WBMDS032G-PKCT34BM-C
	64GB	SBMDS064G-PKCT34BM	WBMDS064G-PKCT34BM-C
	128GB	SBMDS128G-PKCT34BM	WBMDS128G-PKCT34BM-C

◆ APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series – 2280 Form-factor

Product Picture	Grade	Standard grade (0°C ~ 70°C)	Wide Temp. Grade (-40°C ~ +85°C)
	128GB	SBMDS128G-PKCT38BM	WBMDS128G-PKCT38BM-C
	256GB	SBMDS256G-PKCT38BM	WBMDS256G-PKCT38BM-C
	512GB	SBMDS512G-PKCT38BM	WBMDS512G-PKCT38BM-C
	1TB	SBMDS001T-PKCT38BM	WBMDS001T-PKCT38BM-C

Notes:

C : Special conformal coating treated on whole PCBA (Optional)

II. Part Number Decoder:

X1 X2 X3 X4 X5 X6 X7 X8 X9 — **X11 X12 X13 X14 X15 X16 X17 X18** — **X20**

X1 : Grade

S: Standard Grade – operating temp. 0° C ~ 70 ° C

W: Wide Temp. Grade – operating temp. -40° C ~ +85 ° C

X2 : The material of case

B : Bare PCBA w/o Casing

X3 X4 X5 : Product category

MDS : M.2 SATA III host interface

X6 X7 X8 X9 : Capacity

032G: 32GB **256GB:** 256GB

064G: 64GB **512GB:** 512GB

128GB: 128GB **001T** 1TB

X11 : Controller

P : PHANES Series

X12 : Controller version

A, B, C.....

X13 : Controller Grade

C : Commercial grade

X14 : Flash IC

T : Toshiba NAND Flash IC

X15 : Flash IC grade / Type

3 : BiCS 3D-NAND Flash IC.

X16 X17 X18 : Form-Factor

4: 2242 Type

8: 2280 Type

BM: with two notches in B and M positions use up to two PCI Express lanes and provide broader compatibility at the same time

X20 : Reserved for specific requirement

C : Conformal coating (Optional)

Revision History

Revision	Description	Date
1.0	Initial release.	2018/11/29
1.1	Power consumption updated	2019/04/01
2.0	Updated document form	2019/06/13

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1. Introduction

APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series provides high capacity flash memory Solid State Drive (SSD) that electrically complies with SATA Revision 3.2 standard. APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series support SATA 1.5Gbps/3.0Gbps/6.0Gbps data transfer rate with high performance. The available disk capacities are 32GB, 64GB, 128GB, 256GB, 512GB and 1TB. The operating temperature grade is optional for standard grade 0°C ~ 70°C and Wide Temp. grade -40°C ~ +85°C.

APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series provide the ultra-high speed for embedded or server operations with space constraints for host computing systems; the data transfer performance by sequential read is up to 550.0 MB/sec, and sequential write is up to 500.0 MB/sec. which is based on Toshiba's BiCS 3D NAND flash.

APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series PCB design with two notches in B and M positions use up to two PCI Express lanes and provide broader compatibility at the same time for M/B socket mounting, while the M.2 modules with only one notch in the M position use up to four PCI Express lanes; both examples we provide APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series to be a SATA storage devices.

APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series provide a high level interface to the host computer. This interface allows a host computer to issue commands to the APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series to read or write blocks of memory. A powerful hardware design is architecture multiplied LDPC (Low Density Parity Check) for Error Correcting Coding (ECC). APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series intelligent controller manages interface protocols, data storage and retrieval as well as ECC, bad block management and diagnostics, power management and clock control.

Figure1 Shows a block diagram of APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series.

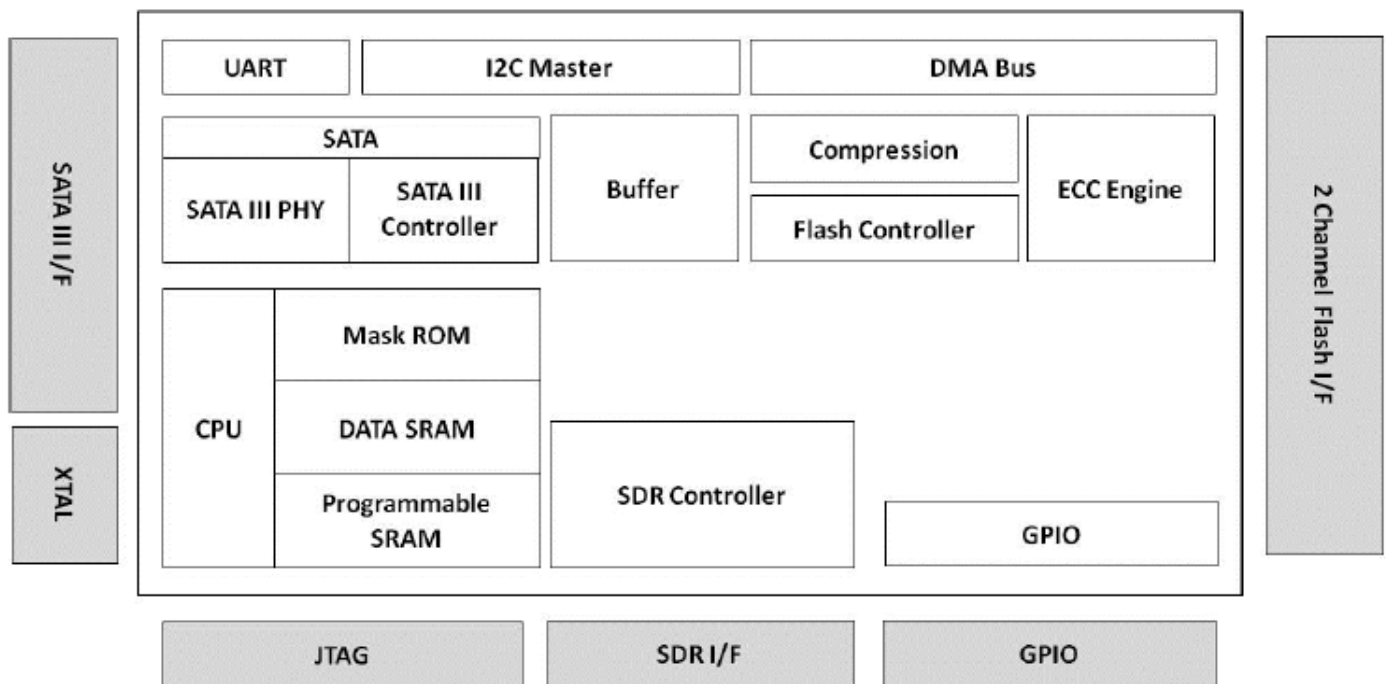


Figure 1: APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series block diagram

1.1. *Scope*

This document describes features, specifications and installation guide of APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series. In the appendix, there provides order information, warranty policy, RMA/DOA procedure for the most convenient reference.

1.2. *Flash Management Technology - Static & Dynamic Wear Leveling*

NAND flash devices can only undergo a limited number of program/erase cycles, and in most cases, the flash media are not used evenly. If some areas get updated more frequently than others, the lifetime of the device would be reduced significantly. Thus, Wear Leveling is applied to extend the lifespan of NAND Flash by evenly distributing write and erase cycles across the media.

APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series provides advanced Wear Leveling algorithm, which can efficiently spread out the flash usage through the whole flash media area. Moreover, by implementing both dynamic and static Wear Leveling algorithms, the life expectancy of the NAND flash is greatly improved.

1.3. *Bad Block Management*

➤ **Early Bad Block**

The fault block generated during the manufacturing process of NAND Flash is called Early Bad Block.

➤ **Later Bad Block**

In the process of use, as the number of operations of writing and erasing increases, a fault block is gradually generated, which is called a Later Bad Block.

Bad block management is a management mechanism for a bad block to be detected by the control IC and mark bad blocks in the NAND Flash and improve the reliability of data access. The bad block management mechanism of the control IC will establish a **Bad Block Table** when the NAND Flash is started for the first time, and will also record the errors found in the process of use in the bad block table, and data is ported to new valid blocks to avoid data loss.

In order to detect the initial bad blocks to handle run time bad blocks, APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series provides the **Bad Block Management** scheme. It remaps a bad block to one of the reserved blocks so that the data contained in one bad block is not lost and new data writes on a bad block is avoided.

1.4. *Error Correcting Coding (ECC)*

APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series provides a high level interface to the host computer. This interface allows a host computer to issue commands to the APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series to read or write blocks of memory.

A powerful hardware design is architecture multiplied LDPC (Low Density Parity Check) for Error Correcting Coding (ECC). APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series intelligent controller manages interface protocols, data storage and retrieval as well as ECC, bad block management and diagnostics, power management and clock control.

1.5. 3D-NAND Flash

3D NAND is a vertical implementation of the NAND flash cell memory array. The memory cell transistors forming the NAND string are connected in a series vertically and the memory transistors are changed from the floating-gate type to a trapped charge type.

In floating-gate technology, die density is increased by shrinking peripheral circuits and active circuits.

With 3D, holding the X/Y dimension of the die constant, die density is increased through multiple layers of the active circuits on the Z axis. Higher-density 3D NAND die enables applications needing high-density NAND chip solutions.

2. Product Specifications

For all the following specifications, values are defined at ambient temperature and nominal supply voltage unless otherwise stated.

2.1. System Environmental Specifications

Table 1: Environmental Specification

APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series		Standard Grade SBMDSxxxG-PKCT3xBM	Wide Temp. Grade WBMDSxxxG-PKCT3xBMC
Temperature	Operating:	0°C ~ +70°C	-40°C ~ +85°C
	Non-operating:	-20°C ~ +80°C	-50°C ~ +95°C
Humidity	Operating & Non-operating:	10% ~ 95% non-condensing	
Vibration	Frequency/Acceleration:	80 Hz to 2000 Hz, 20G, 3 axes	
Shock	Operating & Non-operating:	0.5ms, 1500 G, 3 axes	
Electrostatic Discharge (ESD)	Temperature:	24°C	
	Relative Humidity:	49% (RH)	
	+/-4KV:	Device functions are affected, but EUT will be back to its normal or operational state automatically.	

2.2. System Power Requirements

Table 2: Power Requirement

APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series - 2242		
DC Input Voltage (VCC)		3.3V±5%
Maximum average value	Reading Mode :	1,230.0 mW (max.)
	Writing Mode :	1,336.0 mW (max.)
	Idle Mode :	290.0 mW (max.)
APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series - 2280		
DC Input Voltage (VCC)		3.3V±5%
Maximum average value	Reading Mode :	1,475.0 mW (max.)
	Writing Mode :	1,350.0 mW (max.)
	Idle Mode :	277.0 mW (max.)

2.3. System Performance

Table 3: System Performances

Data Transfer Mode supporting		Serial ATA Gen-III (6.0Gb/s = 768MB/s)					
Maximum Performance	Capacity	32GB	64GB	128GB	256GB	512GB	1TB
	Sequential Read (MB/s)	550.0	550.0	550.0	550.0	550.0	550.0
	Sequential Write (MB/s)	125.0	255.0	450.0	490.0	490.0	500.0

Note:

- The performance was measured using CrystalDiskMarkv5.0; 1GB data size test with SATA 6Gbps host.
- Samples were built using Toshiba BiCS 3D-NAND FLASH
- Performance may differ according to flash configuration and platform.

2.4. System Reliability

Table 4: System Reliability

Wear-leveling Algorithms	Static and Dynamic wear-leveling algorithms	
Bad Block Management	Supportive	
ECC Technology	Hardware design LDPC (Low Density Parity Check)	
Erase counts	TOSHIBA BiCS FLASH™ 3D NAND Flash: 3K P/E Cycles	
TBW (Tera Bytes Written)		
Capacity	32GB	17.0
	64GB	42.0
	128GB	75.0
	256GB	180.0
	512GB	425.0
	1TB	835.0

Note:

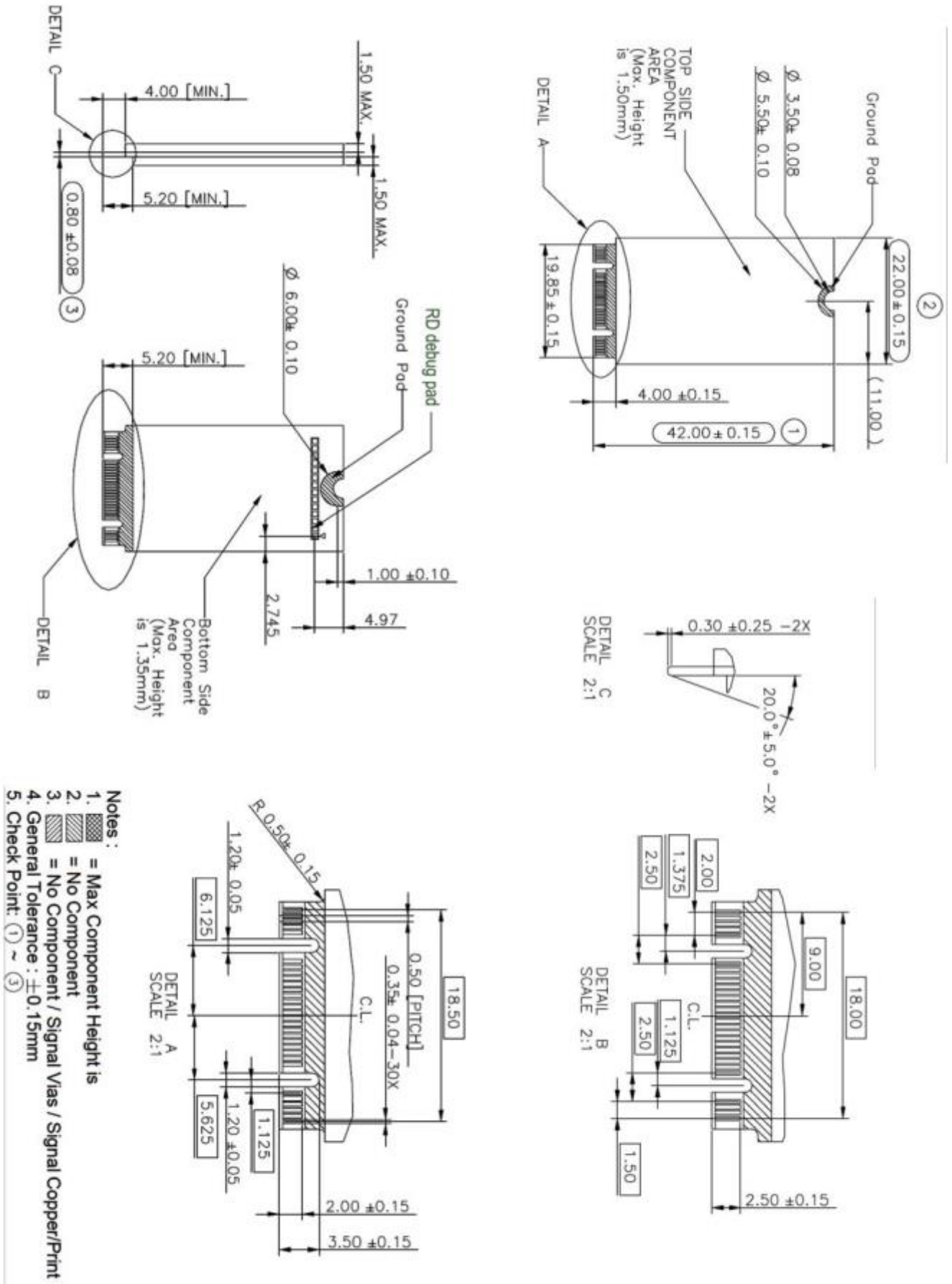
- Client workload by JESD-219A.
- Samples were built using Toshiba BiCS 3D-NAND FLASH
- The endurance of SSD could be varying based on user behavior, NAND endurance cycles, and write amplification factor. It is not guaranteed by flash vendor.

2.5. Physical Specifications

Refer to Table 5 and see Figure 2 for APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series physical specifications and dimensions.

Table 5: Physical Specifications of APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series

Form-Factor	Length:	Width:	Weight:
2242	42.0 mm	22.0 mm	5.00 g / 0.17 oz.
2280	80.0 mm	22.0 mm	8.00 g / 0.28 oz.



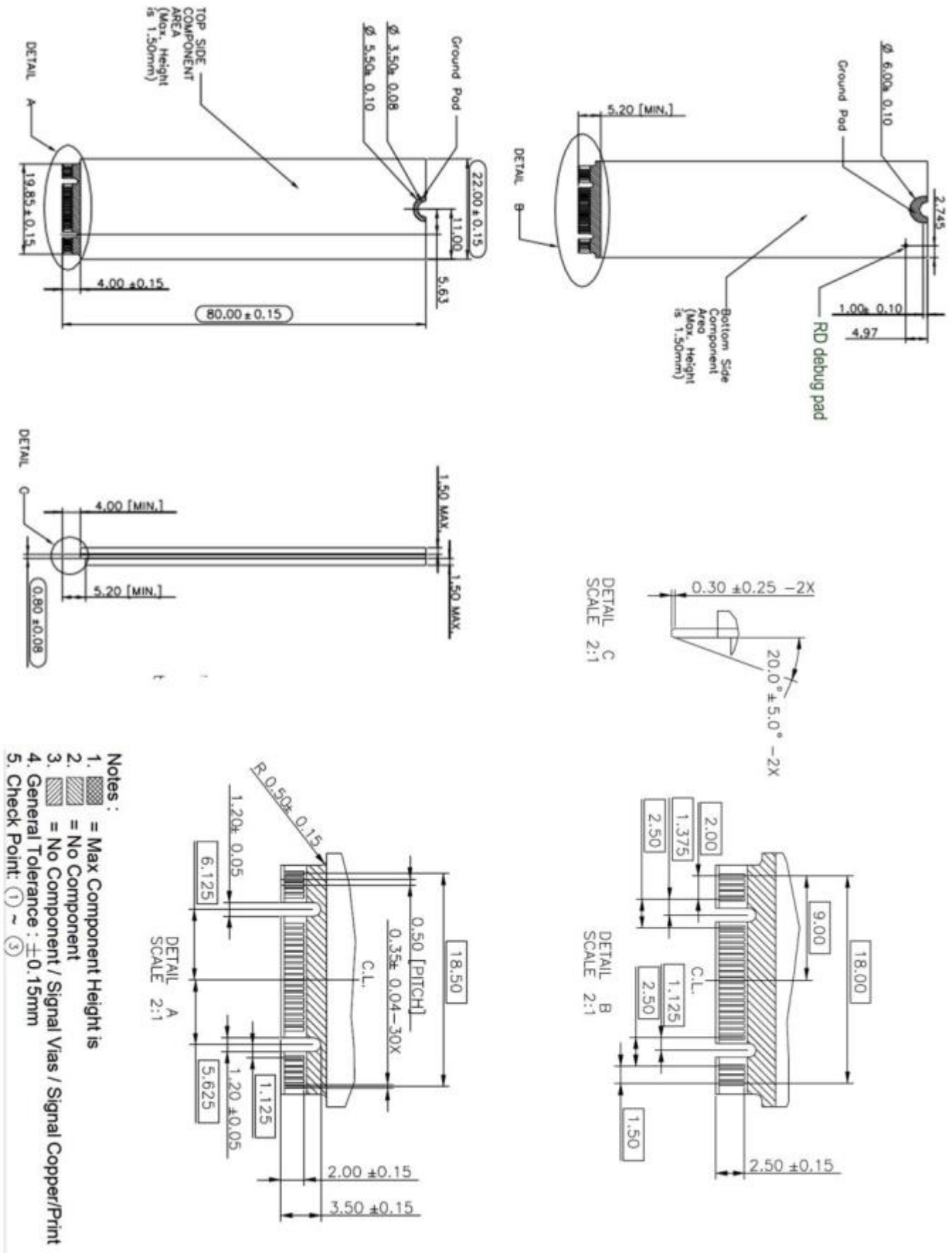


Figure 3: APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series - 2280 Dimension

2.6. Conformal coating

Conformal coating is a protective, dielectric coating designed to conform to the surface of an assembled printed circuit board. Commonly used conformal coatings include silicone, acrylic, urethane and epoxy. APRO applies only silicone on APRO storage products upon requested especially by customers. The type of silicone coating features good thermal shock resistance due to flexibility. It is also easy to apply and repair.

Conformal coating offers protection of circuitry from moisture, fungus, dust and corrosion caused by extreme environments. It also prevents damage from those Flash storages handling during construction, installation and use, and reduces mechanical stress on components and protects from thermal shock. The greatest advantage of conformal coating is to allow greater component density due to increased dielectric strength between conductors.

APRO use MIL-I-46058C silicon conformal coating

3. Interface Description

3.1. M.2 SATA III Module interface

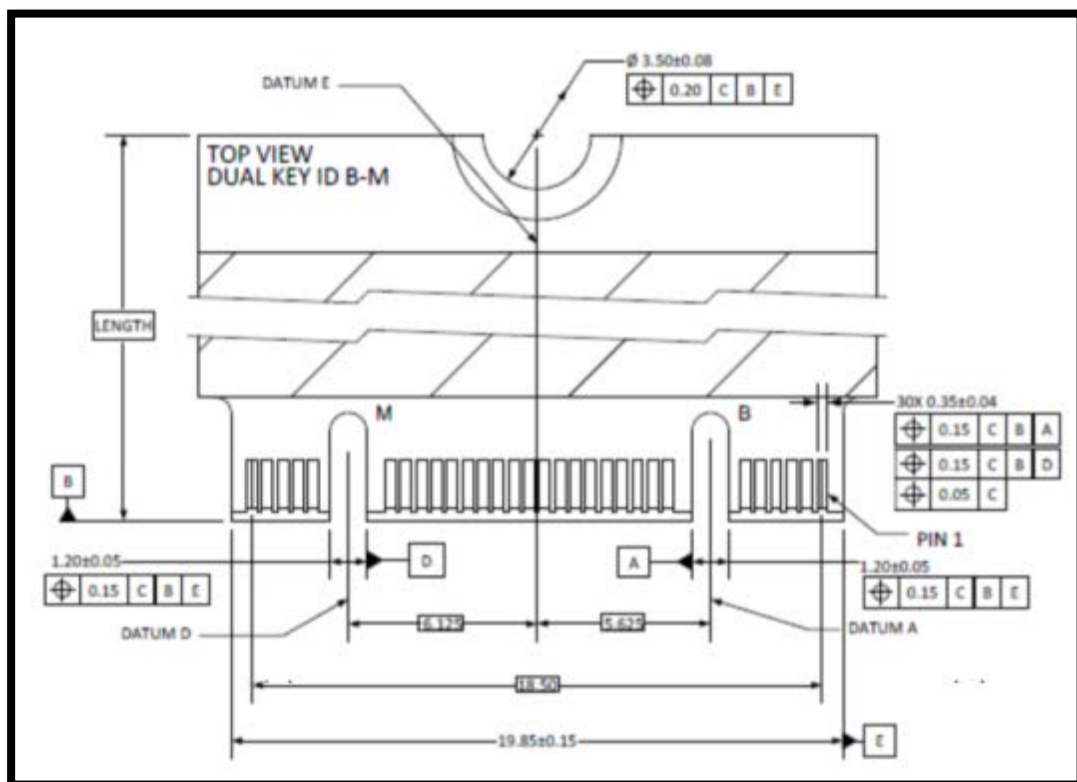


Figure 4: The connectors of Signal Segment and Power Segment

3.2. Pin Assignments

APRO M.2 SATA III Module (3D NAND FLASH) PHANES-K Series operates with standard SATA pin-out. The pin assignments are listed in below table 6.

Table 6 - Pin Assignments

		CONFIG_2 = GND	75
74	3.3V	GND	73
72	3.3V	GND	71
70	3.3V	CONFIG_1 = GND	69
68	SUSCLK(32kHz) (I)(0/3.3V)	N/C	67
	Module Key	Module Key	
	Module Key	Module Key	
	Module Key	Module Key	
	Module Key	Module Key	
58	Reserved for MFG Clock	GND	57
56	Reserved for MFG Data	N/C	55
54	N/C	N/C	53
52	N/C	GND	51
50	N/C	SATA-A+	49
48	N/C	SATA-A-	47
46	N/C	GND	45
44	N/C	SATA-B-	43
42	N/C	SATA-B+	41
40	N/C	GND	39
38	DEVSLP (I)(0/3.3V)	N/C	37
36	N/C	N/C	35
34	N/C	GND	33
32	N/C	N/C	31
30	N/C	N/C	29
28	N/C	GND	27
26	N/C	N/C	25
24	N/C	N/C	23
22	N/C	CONFIG_0 = GND	21
20	N/C	Module Key	
	Module Key	Module Key	
	Module Key	Module Key	
	Module Key	Module Key	
	Module Key	Module Key	
10	DAS/DSS# (O)(OD)	N/C	11
8	N/C	N/C	9
6	N/C	N/C	7
4	3.3V	N/C	5
2	3.3V	GND	3
		CONFIG_3 = GND	1

Appendix A: Limited Warranty

APRO warrants your SATA III M.2 SSD (3D NAND FLASH) PHANES-K Series against defects in material and workmanship for the life of the drive. The warranty is void in the case of misuse, accident, alteration, improper installation, misapplication or the result of unauthorized service or repair. The implied warranties of merchantability and fitness for a particular purpose, and all other warranties, expressed or implied, except as set forth in this warranty, shall not apply to the products delivered. In no event shall APRO be liable for any lost profits, lost savings or other incidental or consequential damages arising out of the use of, or inability to use, this product.

BEFORE RETURNING PRODUCT, A RETURN MATERIAL AUTHORIZATION (RMA) MUST BE OBTAINED FROM APRO.

Product shall be returned to APRO with shipping prepaid. If the product fails to conform based on customers' purchasing orders, APRO will reimburse customers for the transportation charges incurred.

WARRANTY PERIOD:

- **3D NAND FLASH (Standard grade / Wide Temp. grade) 2 years / Within 3K Erasing Counts**

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